

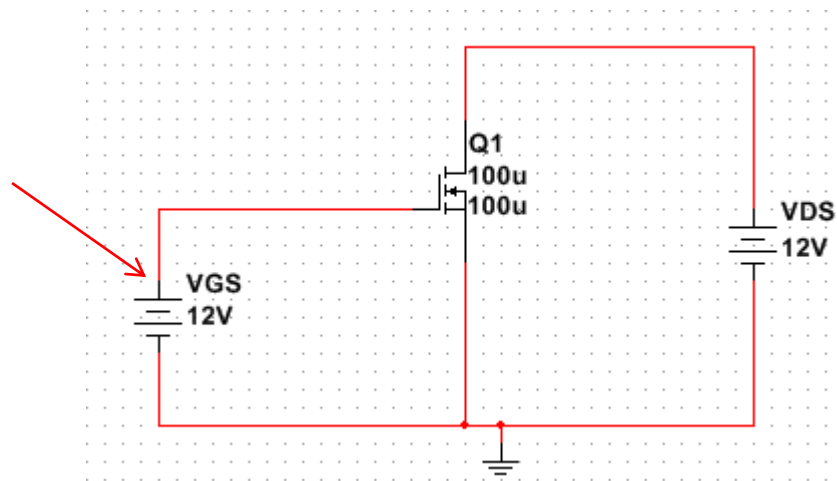
EXPERIMENT TWO

I/V characteristics of Enhancement MOSFET

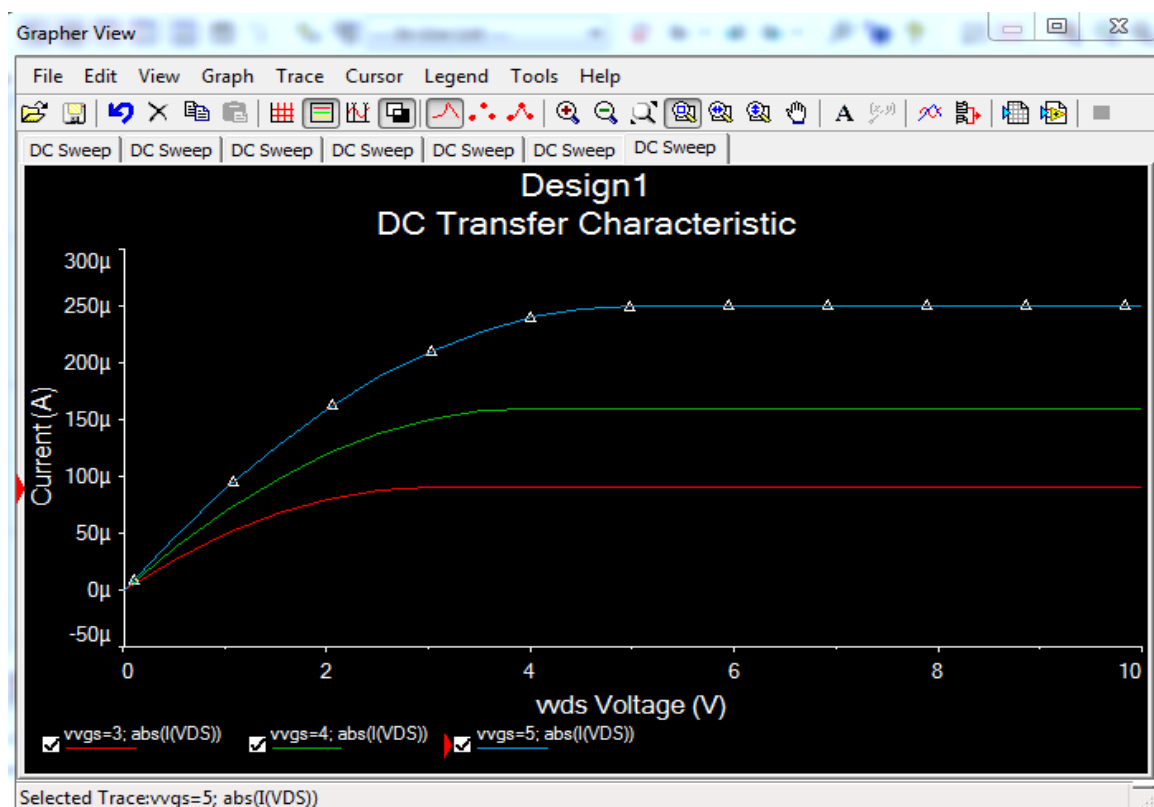
AIM: Study the relationship between drain current (I_D) and gate source voltage (V_{GS}).

APPARATUS: Enhancement MOSFET (Virtual transistor), breadboard, 2 D.C power supply and Ground.

Circuit Diagram:



Output:



Procedure: